



PATENT ABSTRACTS OF JAPAN

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(57) Abstract:

PROBLEM TO BE SOLVED: To achieve a process for forming Cu wiring on an organic interlayer insulation, and to reduce effects due to wiring delay.

SOLUTION: In this manufacture of a semiconductor device, an organic interlayer insulation film 78 is formed in the uppermost of a multilayer organic interlayer insulation film, a first etching stopper 80 is formed on the organic interlayer insulation film 78, and by forming a second etching stopper film 82 that is different from the first etching stopper film 80 on the first etching stopper film 80, simultaneous formation of a wiring groove 91 and a contact hole 89 is made possible.

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